

DC Member 6 - 5-year Publication details

Member from Other Univeristy

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Area of Specialization: - **Device Modelling and Simulation, Quantum transport in low dimensional systems, MOS Device physics, Photodetectors, NEMS**

List of Publication: -

- [1] “Influence of Temperature on p-GaN HEMT for High Power Application”, N Geddam, B Snega, A Pon, A Bhattacharyya, R Ramesh, 5th International Conference on Devices, Circuits and Systems (ICDCS), 2020
- [2] “Insights on Si doping on PNRs for NDR with high PVR and diode behaviour with a high rectification ratio”, S Carmel, A Pon, R Ramesh, A Bhattacharyya Physica E: Low-dimensional Systems and Nanostructures 114, 113630, 2019
- [3] “Optimization of the geometry of a charge plasma double-gate junctionless transistor for improved RF stability”, A Pon, A Bhattacharyya, B Padmanaban, R Ramesh, Journal of Computational Electronics 18 (3), 906-917, 2019
- [4] “Effect of interface trap charges on the performance of asymmetric dielectric modulated dual short gate tunnel FET”, A Pon, KSVP Tulasi, R Ramesh, AEU-International Journal of Electronics and Communications 102, 1-8, 2019

- [5] “Influence of Temperature on the Performance of Dual Gate Phosphorene TFET”, A Pon, S Carmel, A Bhattacharyya, R Ramesh, International Conference on Vision Towards Emerging Trends, 2019
- [6] “Effect of Edge passivation on the Electronic Properties of Zigzag Phosphorene Nanoribbons (ZPNRs) Antidots”, S Carmel, A Pon, R Ramesh, A Bhattacharyya, Conference on Emerging Devices and Smart Systems (ICEDSS), 171-174, 2018
- [7] “Spacer Effects on the Circuit Performance of DG Junctionless Transistor”, A Pon, M Madheswaran, AS Carmel, A Bhattacharyya, R Ramesh, Conference on Emerging Devices and Smart Systems (ICEDSS), 167-170, 2018
- [8] “Bandgap scaling and negative differential resistance behavior of zigzag phosphorene antidot nanoribbons (ZPANRs)”, S Carmel, A Pon, N Meenakshisundaram, R Ramesh, A Bhattacharyya, Physical Chemistry Chemical Physics 20 (21), 14855-14863, 2018
- [9] “Performance analysis of asymmetric dielectric modulated dual short gate tunnel field effect transistor”, A Pon, AS Carmel, A Bhattacharyya, R Ramesh, Superlattices and Microstructures 113, 608-615, 2018
- [10] “ZigZag Phosphorene Nanoribbons Antidot—Electronic Structure and Device Application”, S Carmel, A Pon, R Ramesh, A Bhattacharyya, International Workshop on the Physics of Semiconductor and Devices, 7-13, 2017
- [11] “Channel and gate engineered dielectric modulated asymmetric dual short gate TFET”, R Ramesh, A Pon, S Carmel, A Bhattacharyya, International conference on Microelectronic Devices, Circuits, 2017
- [12] “Calculation of electronic and transport properties of phosphorene nanoribbons using DFT and semi empirical models”, AS Carmel, A Pon, R Ramesh, A Bhattacharyya, International conference on Microelectronic Devices, Circuits, 2017
- [13] “Nanoscale circuit implementation using tri-metal gate engineered nanowire MOSFET with gate stack for analog/RF applications”, A Bhattacharyya, R Ramesh, Journal of Computational Electronics 16 (1), 155-161, 2017
- [14] “Influence of gate and channel engineering on multigate MOSFETs”, R Ramesh, Microelectronics Journal 66, 136-154, 2017

- [15] “Modelling and simulation of tri-material gate stack gate all-around (TMGSGAA) MOSFET using Legendre Wavelets for analog/RF applications”, R Ramesh, A Bhattacharyya, Superlattices and Microstructures 97, 575-585, 2016
- [16] “Numerical modeling of high sensitivity nanoscale FinFET biosensor for health care applications”, R Ramesh, K Kannan, M Madheswaran, Conference on Emerging Devices and Smart Systems (ICEDSS), 9-12, 2016
- [17] “Hot-carrier reliability on the optical characteristics of gate stack gate all-around (GSGAA) MOSFET considering quantum mechanical effects”, M Madheswaran, R Ramesh, K Kannan, Optik 127 (5), 2694-2702, 2016
- [18] “Numerical modeling on the optical characteristics of triple material gate stack gate all-around (TMGSGAA) MOSFET”, R Ramesh, M Madheswaran, K Kannan, Superlattices and Microstructures 85, 418-432, 2015
- [19] “Numerical modeling of triple material gate stack gate all-around (TMGSGAA) MOSFET considering quantum mechanical effects”, B Padmanaban, R Ramesh, D Nirmal, S Sathiyamoorthy, Superlattices and Microstructures 82, 40-54, 2015

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